

Standard Rectifier Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

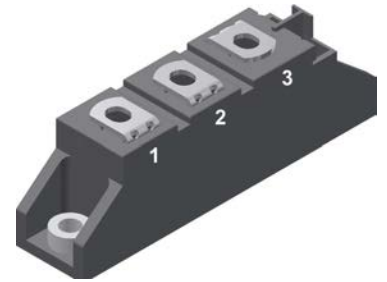
$$I_{FAV} = 35 \text{ A}$$

$$V_F = 1,1 \text{ V}$$

Phase leg

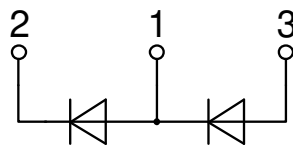
Part number

MDMA35P1200TG



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: TO-240AA

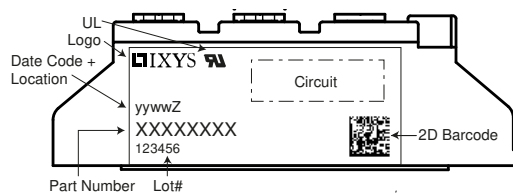
- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_R	reverse current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			20	μA
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			1,5	mA
V_F	forward voltage drop	$I_F = 35\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1,15	V
		$I_F = 70\text{ A}$				1,34	V
		$I_F = 35\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1,10	V
		$I_F = 70\text{ A}$				1,35	V
I_{FAV}	average forward current	$T_C = 100^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}\text{C}$			35	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0,83	V
r_F	slope resistance					7,3	m Ω
R_{thJC}	thermal resistance junction to case					0,9	K/W
R_{thCH}	thermal resistance case to heatsink				0,2		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				130	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}\text{C}$			500	A
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			540	A
		$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}\text{C}$			425	A
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			460	A
I^2t	value for fusing	$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}\text{C}$			1,25	kA ² s
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			1,22	kA ² s
		$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}\text{C}$			905	A ² s
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$			880	A ² s
C_J	junction capacitance	$V_R = 400\text{ V; } f = 1\text{ MHz}$			19		pF

Package TO-240AA				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				200	A
T_{VJ}	virtual junction temperature			-40		150	°C
T_{op}	operation temperature			-40		125	°C
T_{stg}	storage temperature			-40		125	°C
Weight					76		g
M_D	mounting torque			2,5		4	Nm
M_T	terminal torque			2,5		4	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13,0	9,7			mm
$d_{Spb/Apb}$		terminal to backside	16,0	16,0			mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4800			V
		t = 1 minute		4000			V



Part description

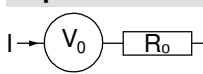
M = Module
 D = Diode
 M = Standard Rectifier
 A = (up to 1800V)
 35 = Current Rating [A]
 P = Phase leg
 1200 = Reverse Voltage [V]
 TG = TO-240AA

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA35P1200TG	MDMA35P1200TG	Box	36	515021

Equivalent Circuits for Simulation

* on die level

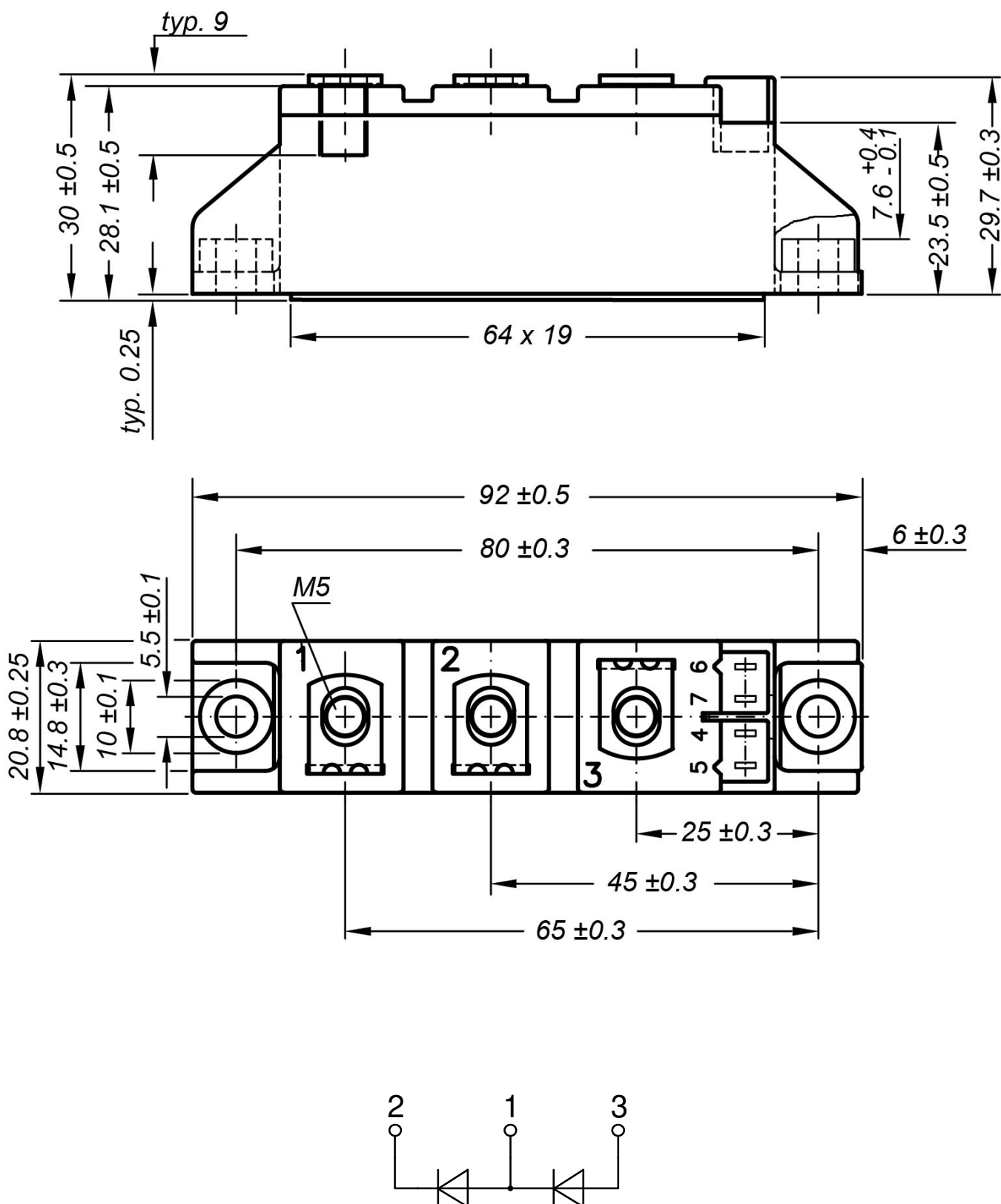
$T_{VJ} = 150^{\circ}\text{C}$



Rectifier

$V_{0 \max}$	threshold voltage	0,83	V
$R_{0 \max}$	slope resistance *	6,1	mΩ

Outlines TO-240AA



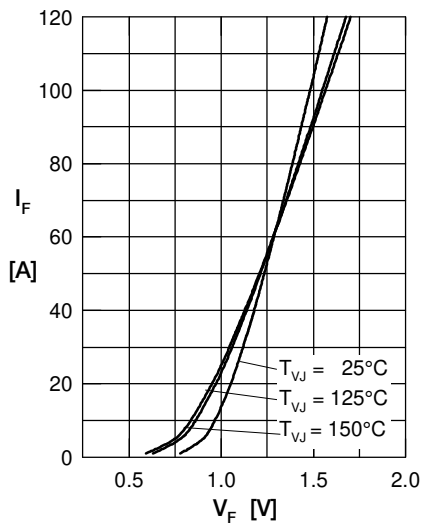
Rectifier


Fig. 1 Forward current versus voltage drop per diode

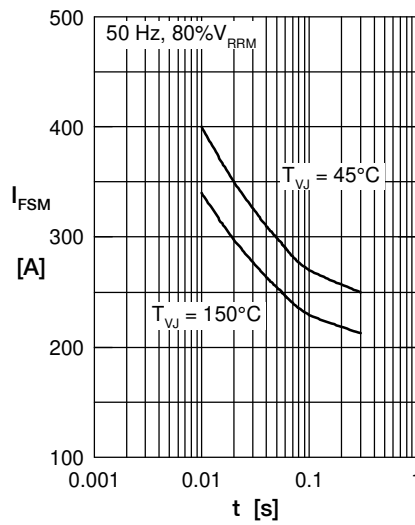


Fig. 2 Surge overload current vs. time per diode

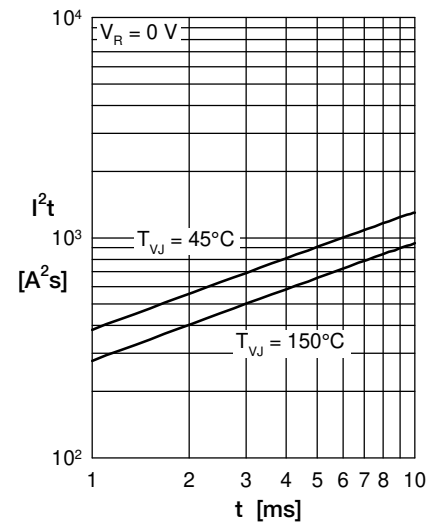
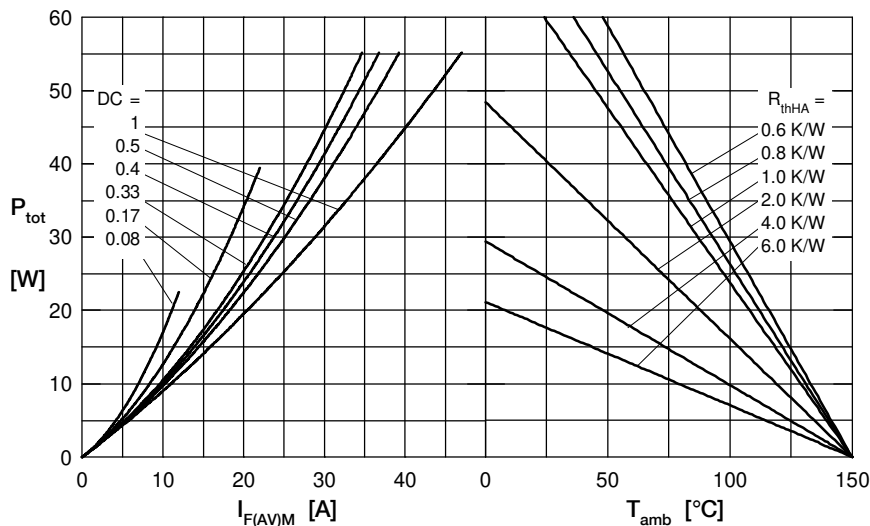

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

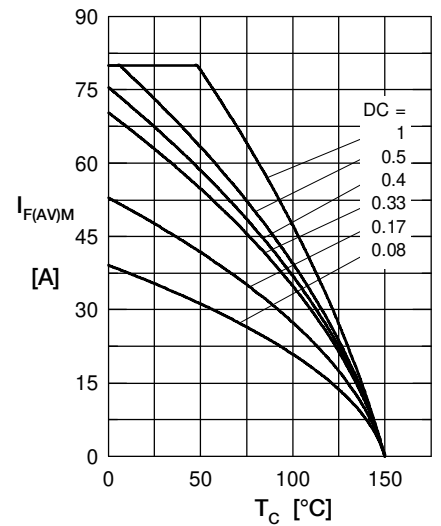


Fig. 5 Max. forward current vs. case temperature per diode

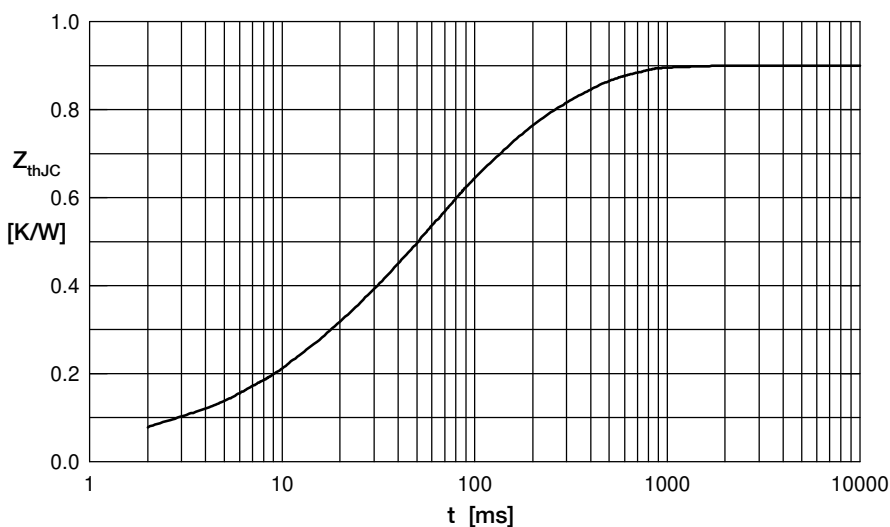


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.042	0.001
2	0.128	0.010
3	0.425	0.050
4	0.305	0.230